4. (Original): A microelectronic structure according to claim 1, wherein said metal layer comprises Cu or Cu alloy.

5. (Original): A microelectronic structure according to claim 1, wherein said metal layer comprises Al or Al alloy.

6. (Original): A microelectronic structure according to claim 1, wherein said layer of high dielectric constant material comprises a complex metal oxide selected from the group consisting of $SrBi_2Ta_2O_9$ (SBT), $(Ba,Sr)TiO_3$ (BST), $BiTaO_4$ (BT), and $Pb(Zr,Ti)O_3$ (PZT).

7. (Original): A microelectronic structure according to claim 1, wherein said layer of high dielectric constant material comprises perovskite BST material.

8. (Original): A microelectronic structure according to claim 1, wherein said layer of high dielectric constant material comprises amorphous BST material.

9. (Original): A microelectronic structure according to claim 1, wherein said conductive barrier layer has a thickness in a range of from about 1nm to about 100nm.

10. (Original): A microelectronic structure according to claim 1, wherein said conductive barrier layer has a thickness in a range of from about 5nm to about 20nm.

11. (Original): A microelectronic structure according to claim 1, wherein said conductive barrier layer comprises Pt.

12. (Original): A microelectronic structure according to claim 1, wherein said conductive barrier layer comprises Ir.